

[CMOS IMAGE SENSOR DEVICE AND PROCESS OF PRODUCING THE SAME]

Abstract of Disclosure

A CMOS image sensor device including a substrate, a photodiode sensing region, a reset transistor, a source follower transistor and a buried contact (BC) is provided. The substrate has an isolation structure that defines an active region. The photodiode sensing region is located in the substrate, and the reset transistor is located on the active region of the substrate and has a source region partially connected to the photodiode sensing region. A first end of the buried contact is located on the substrate between the photodiode sensing region and the reset transistor and extends over the isolation structure to cover the periphery of the isolation structure and electrically connect the source region of the reset transistor. A second end of the buried contact is located on the active region of the substrate to be used as a gate of the source follower transistor.

Figures

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